

Molecular orientation and weak-charge transfer dynamics of PTCDI-C4 molecules on MoS₂ interfaces



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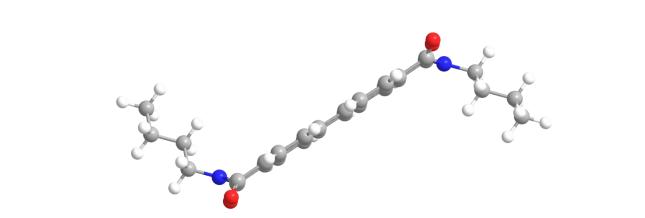
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Abstract

Two-dimensional layered semiconductors have proven to be versatile examples in the exploration of their unique layer-number dependent electronic and optical properties. Recent progress on altering the physical properties of transition metal dichalcogenides (TMDCs) using surface molecular doping effect has much interest.[1-2] In this study, we investigate the molecular alignment and the ultrafast charge transfer dynamics of N,N`-DibutyI-3,4,9,10-perylenedicarboximide (PTCDI-C4) molecules at different molecular thicknesses on molybdenum disulphide (MoS_2) substrates using near edge X-ray absorption fine structure spectroscopy (NEXAFS) and Resonant Photoemission (RPES), respectively. The average tilt angle analysis revealed a strong anisotropy in the π^* symmetry transition (284-288 eV range) across the absorption threshold. The non-planar molecular configuration was extracted from the carbon K-edge of the perylene spectrum.[3] Core hole clock spectroscopies at the few monolayer sample displayed a resonant enhancement of the occupied state level which indicates the existence of a moderate interfacial electronic coupling between the adsorbed molecules and substrate. These findings provide a deeper understanding of the interfacial interaction of organic semiconductors on transition metal dichalcogenide surfaces, which is essential for the development of non-planar geometry-based organic devices.

Background

NEXAFS results



The perylene derivative family is one of the most extensively studied organic semiconductor in the field of organic electronics

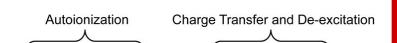
TMDCs are exotic materials of current interest especially 2D van der Waal in heterostructures due to their band gap tunable properties

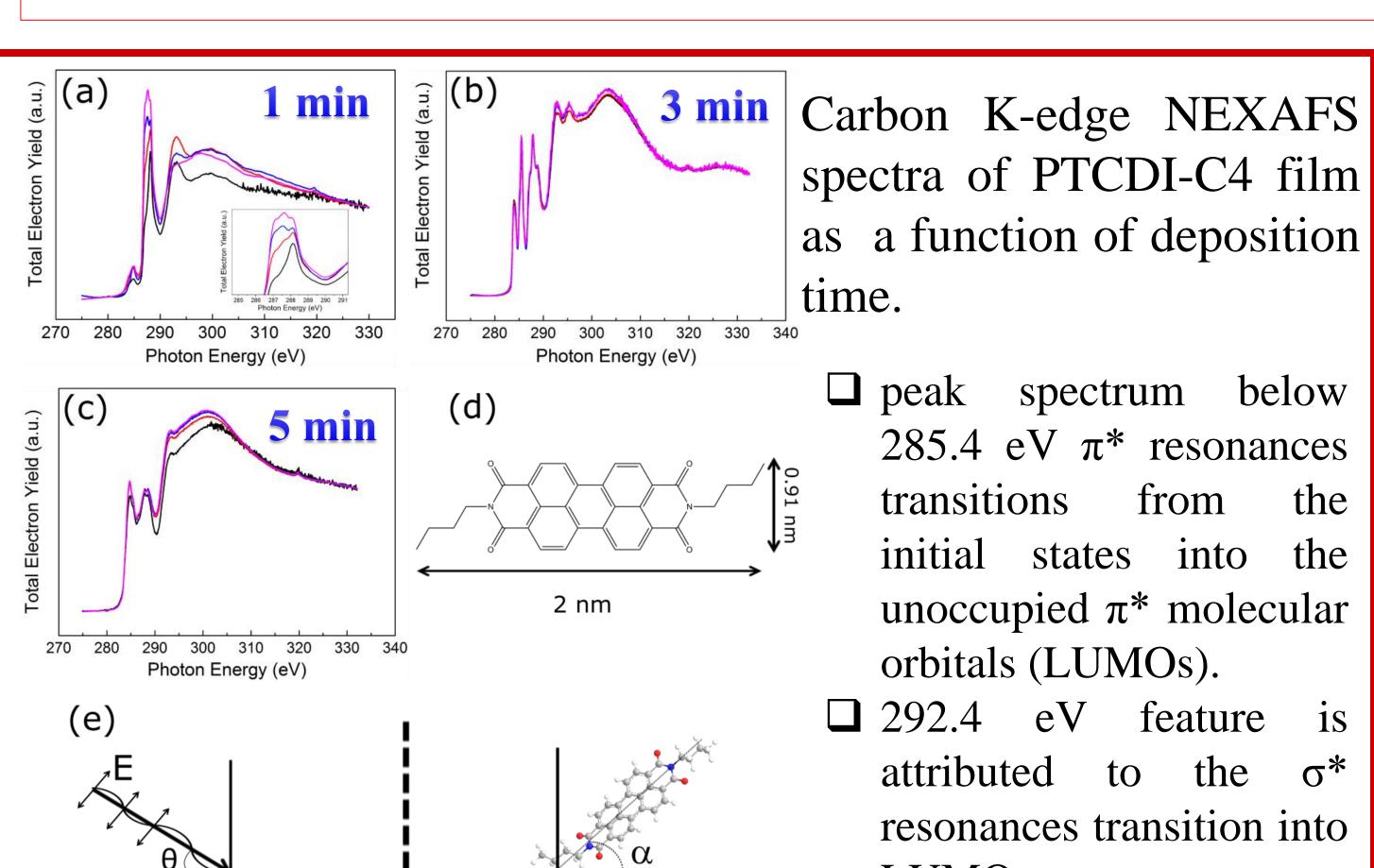
Goal

To investigate the molecular orientation and the charge transfer dynamics of the hybrid organic/inorganic heterostructures.

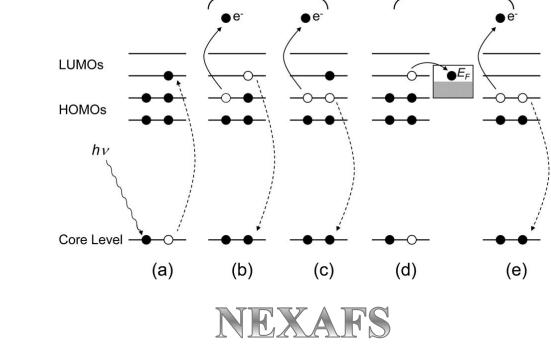
Synchroton radiation technique

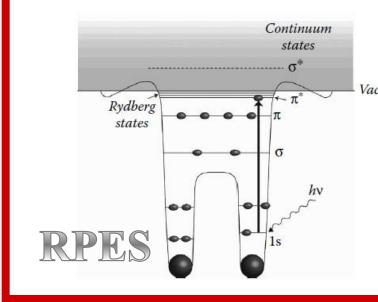
SINS : Surface, Interface and Nanostructure Science







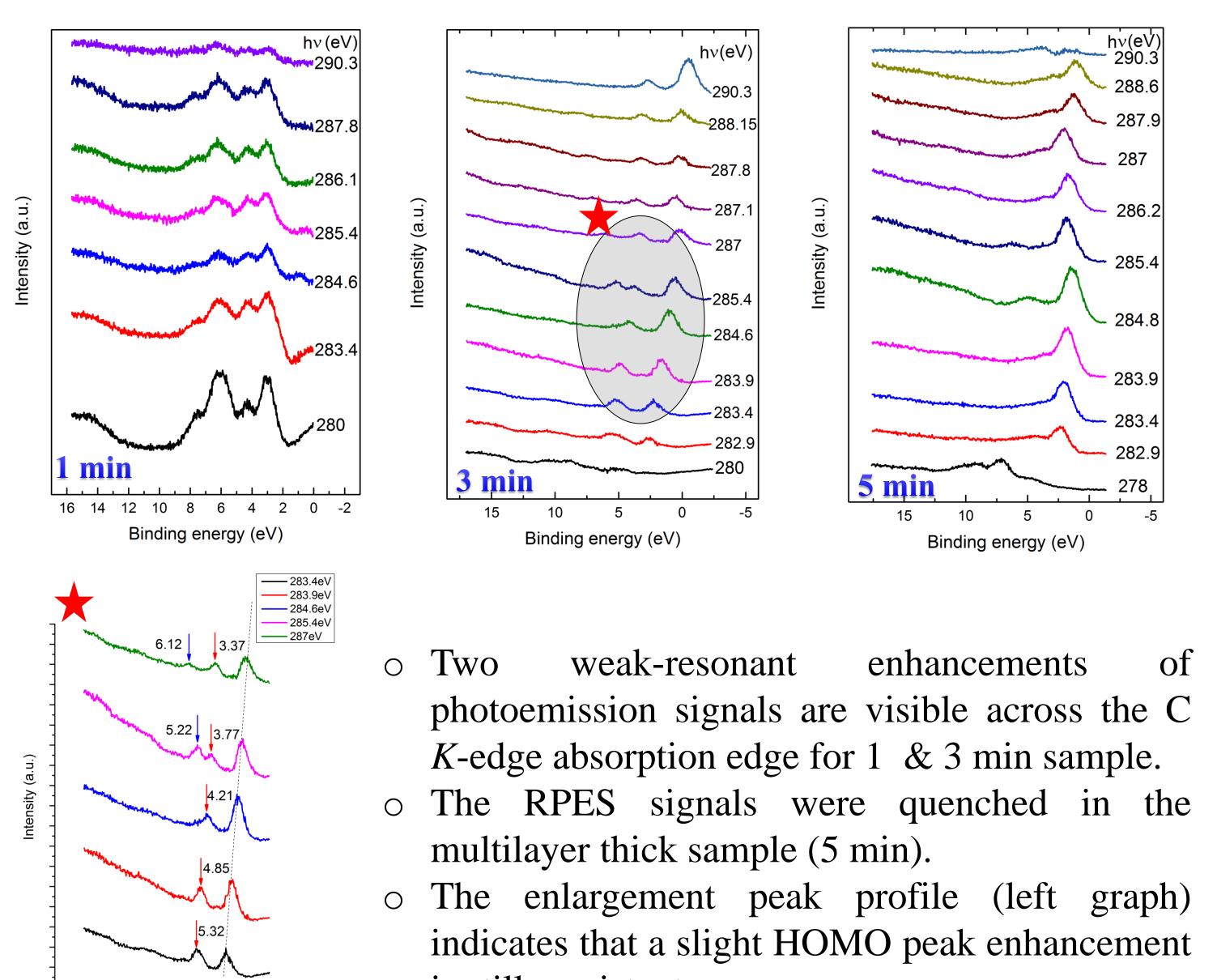




Binding energy (eV)

Thermally-sublimated samples were probed using synchrotron based resonant photoemission spectroscopy (RPES) and nearedge X-ray absorption fine structure (NEXAFS) spectroscopy.

RPES results



Linear plots of *I* versus $\cos^2\Theta$ were used to

extract the slope and intercept $\rightarrow \alpha$

LUMOs.

Average tilt angle

$$a A \cdot \left\{ \frac{P}{3} \left[1 + \frac{1}{2} \left(3\cos^2 \Theta - 1 \right) \left(3\cos^2 \alpha - 1 \right) \right] + \frac{(1-P)}{2} \sin^2 \alpha \right\}$$

Sample	average tilt angle (α)
1 min	$62.3^{\circ} \pm 0.1^{\circ}$
3 min	$55.0^{\circ} \pm 0.9^{\circ}$
5 min	$55.8^{\circ} \pm 0.3^{\circ}$

For 1 min sample, we can deduce that the molecule has a stronger tendency to stand upright with respect to the MoS₂ surface. The extracted tilt angles for the other two thicker samples are close to the magic angle (54.7°), implying that a random PTCDI-C4 molecular orientation exists in the multilayer samples.

Summaries

is still persistent.

- . A polarization dependence is clearly resolved in the case of submonolayer coverage (1 min). In contrast, the degree of polarization of the other two cases (3 min and 5 min) showed negligible changes in both π^* and σ^* electronic transition as a function of incident photon angle.
- Thickness-dependent of RPES profile suggested that a weak electronic coupling was established at the PTCDI-C4/MoS₂ interface.

References

[1] Mak, K. F. et al., Atomically thin MoS_2 : a new direct-gap semiconductor. Phys. Rev. Lett. 105, 136805 (2010). [2] Chhowalla, M. et al., The chemistry of two-dimensional layered transition metal dichalcogenide nanosheets. Nature Chem. 5, 263-275 (2013). [3] Arramel et.al., *submitted*, (2016).

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